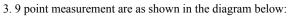
Icemos Technology Ltd Product Specification 1000.548101 Issue Date 03 October 2018 11:5

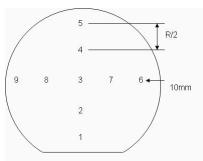
Part Number Customer

Category	Parameter		Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm		
	2.0	Primary Flat Orientation	{110}+/-0.5 degree	Wafer Vendor	
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor	
	4.0	Secondary Flat Orientation	none		
	5.0	Overall Thickness	627.00 +/- 26.10 μm	ADE, 100%	
	6.0	Total Thickness Variation (TTV)	<5.00μm	Guaranteed by Process	
	7.0	Bow	<60.00μm	ADE to ASTM F534, 20%	
	8.0	Warp	<60.00μm	ADE to ASTM F657, 20%	
	9.0	Edge Chips	0	Bright Light, 100% (note 2)	
	10.0	Edge Exclusion	3mm		
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor	
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor	
	13.0	Handle Thickness	525.00 +/- 25.00 μm	ADE, 100%	
	14.0	Handle Doping Type	N	Wafer Vendor	
	15.0	Handle Dopant	Phosphorous	Wafer Vendor	
	16.0	Handle Resistivity	1 - 50 Ohmem	Wafer Vendor	
	17.0	Backside Finish	Polished, with oxide and lasermark	Wafer Vendor	
BuriedOxide	18.0	Oxide Type	Thermal		
	19.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%	
	20.0	Oxide formed on	Handle and Device Wafer		
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor	
	22.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor	
	23.0	Nominal Thickness	100.00 +/- 1.00 μm	FTIR, 100% 9-Pt (note3)	
	24.0	Distance to device silicon edge from wafer edge	Edge Removal < 2.0mm	Microscope Inspection	
	25.0	Edge Removal Angle	45 +/- 15deg	Graranteed by process	
	26.0	Edge Removal Depth in Handle	<100um	Guaranteed by process	
	27.0	Device Doping Type	N	Wafer Vendor	
	28.0	Device Dopant	Phosphorous	Wafer Vendor	
	29.0	Device Resistivity	1 - 10 Ohm-cm	Wafer Vendor	
	30.0	Buried Layer Implant	none	implant vendor	
	31.0	Oxygen Concentration	<12.6 ppma	Wafer Vendor	
	32.0	Voids	All wafers scanned for voids by Scanning Acoustic Microscope (SAM)	SAM & Bright Light, 100% (note 2). Void spec as per comments below.	
	33.0	Scratches	0	Bright Light, 100% (note 2)	
	34.0	Haze	none	Bright Light, 100% (note 2)	

Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspec	tion performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall			

Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.





Additional Information